

1N5614 1N5620
1N5616 1N5622
1N5618

**GLASS PASSIVATED
SILICON RECTIFIERS
1.0 AMP, 200 THRU 800 VOLT**



GPR-1A CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N5614 series types are silicon rectifiers mounted in a hermetically sealed, glass passivated package, designed for general purpose applications where high reliability is desired.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	1N5614	1N5616	1N5618	1N5620	1N5622	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current ($T_A=55^{\circ}\text{C}$)	I_O			1.0			A
Peak Forward Surge Current, $t_p=8.3\text{ms}$	I_{FSM}			40			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +200			$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

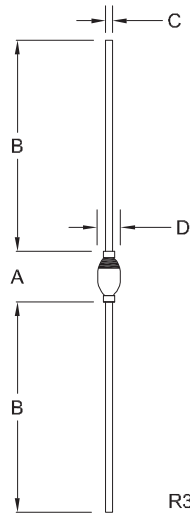
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		0.5	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=100^{\circ}\text{C}$		25	μA
BV_R	$I_R=50\mu\text{A}$ (1N5614)	220		V
BV_R	$I_R=50\mu\text{A}$ (1N5616)	440		V
BV_R	$I_R=50\mu\text{A}$ (1N5618)	660		V
BV_R	$I_R=50\mu\text{A}$ (1N5620)	880		V
BV_R	$I_R=50\mu\text{A}$ (1N5622)	1100		V
V_F	$I_F=1.0\text{A}$		1.2	V
C_J	$V_R=12\text{V}, f=130\text{kHz}$		35	pF
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$		2.0	μs

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GPR-1A CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	-	0.240	-	6.10
B	1.000	-	25.40	-
C	0.028	0.034	0.71	0.86
D	0.070	0.150	1.80	3.81

GPR-1A (REV: R3)

MARKING: FULL PART NUMBER

R3 (27-February 2013)